

ABSTRACT

A semiconductor device is provided with a FET having a sufficiently small short channel effect as well as sufficiently small junction capacitance and junction leak current. The FET comprises a channel region formed in a silicon substrate, a gate electrode formed on the channel region through the intermediary of a gate insulting film, heavily doped regions, and pocket regions. The pocket regions are formed so as to extend from inside the heavily doped regions, respectively, over inside the channel region. Because a pocket sub-region inside the respective heavily doped regions is formed so as to be located in regions shallower than the respective lower end faces of the heavily doped regions, junction capacitance and junction leak current are reduced. Further, because respective pocket sub-regions inside the channel region are formed in regions deeper than the respective pocket sub-regions inside the heavily doped regions, a short channel effect can be reduced.